

M-plane GaN Substrates

| Features | Units | Conductivity | | |
|--|----------------------|--|--------|----|
| | | n-type | p-type | SI |
| Carrier concentration | cm ⁻³ | ~ 10 ¹⁹ | - | - |
| Resistivity | Ω·cm | 10 ⁻³ - 10 ⁻² | - | - |
| Mobility | cm ² /V·s | ~ 150 | - | - |
| Thickness | μm | 300-400 | - | - |
| Total thickness variation (TTV) | μm | ~ 20 | - | - |
| Bow | μm | ≤ 10 | - | - |
| FWHM of X-ray rocking curve, (epi-ready surface at 100 μm x 100 μm slit) | arcsec | ~ 30 | - | - |
| Dislocation density | cm ⁻² | < 10 ⁵ | - | - |
| Misorientation | deg | On demand | | |
| Surface finishing | | As cut / ground Roughly polished Optically polished (RMS < 3 nm) Epi-ready (RMS < 0.5 nm) | | |
| Available sizes | mm | 10x10, 13x15 | | |
| Packaging | | Separate single wafer container | | |
| Special Order Option | | Please, contact Sales Department | | |

